

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10039284	FILING DATE 12/31/2001	CLASS 257	SUBCLASS 2	GAU <i>200, Phat</i>	EXAMINER <i>2811</i>
----------------------	---------------------------	--------------	---------------	-------------------------	-------------------------

**APPLICANTS: Blanchard Richard; Hsieh Fwu-luan;
2811

**CONTINUING DATA VERIFIED:

BEST AVAILABLE COPY

** FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 35 USC 119 conditions met Verified and Acknowledged Examiners's initials		<input type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> yes <input type="checkbox"/> no	ATTORNEY DOCKET NO GS 174

TITLE : High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching using an etchant gas that is also a doping source
U.S. DEPT. OF COMM (PAT. & TM-PTC-436LRv. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Assistant Examiner	
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drawg.	Figs. Drawg.
TERMINAL DISCLAIMER		Primary Examiner	
		PREPARED FOR ISSUE	
		Application Examiner	
WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368. Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.			

FILED WITH

DISK (CRF)

(Attached in pocket on right inside flap)

CD-ROM